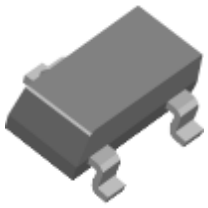
P-Channel 20-V (D-S) MOSFET

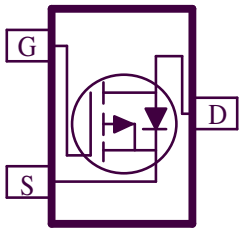
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (OHM)	I_D (A)
-20	0.100 @ V_{GS} = -4.5V	-2.9
	0.160 @ V_{GS} = -2.5V	-2.3
	0.290 @ V_{GS} = -1.8V	-1.7

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology

Pb-free
RoHS COMPLIANT
HALOGEN FREE





ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±12	
Continuous Drain Current[a]	T_A=25°C	I_D	-2.9	A
	T_A=70°C		-2.4	
Pulsed Drain Current[b]		I_{DM}	-10	
Continuous Source Current (Diode Conduction)[a]		I_S	±1.6	A
Power Dissipation[a]	T_A=25°C	P_D	1.25	W
	T_A=70°C		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient[a]	t <= 5 sec	R_{THJA}	100	°C/W
	Steady-State		166	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min	**Typ**	**Max**	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 uA	-0.4			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = +/-12 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -16 V, V_{GS} = 0 V			-1	uA
		V_{DS} = -16 V, V_{GS} = 0 V, T_J = 55°C			-10	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = -5 V, V_{GS} = -4.5 V	-3			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = -4.5 V, I_D = -2.9 A			0.100	Ω
		V_{GS} = -2.5 V, I_D = -2.3 A			0.160	
		V_{GS} = -1.8 V, I_D = -1.7 A			0.290	
Forward Tranconductance[A]	g_{fs}	V_{DS} = -5 V, I_D = -2.8 A		3		S
Diode Forward Voltage	V_{SD}	I_S = -1.6 A, V_{GS} = 0 V		-0.7		V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = -5 V, V_{GS} = -4.5 V, I_D = -2.6 A		6		nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			1.3		
Input Capacitance	C_{iss}	P-Channel VDS=-15V, VGS=0V, f=1MHz		395		pF
Output Capacitance	C_{oss}			130		
Reverse Transfer Capacitance	C_{rss}			33		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -5 V, R_L = 5 OHM, V_{GEN} = -4.5 V, R_G = 6 OHM		6.5		ns
Rise Time	t_r			3		
Turn-Off Delay Time	$t_{d(off)}$			31		
Fall-Time	t_f			4		

Notes

a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

Typical Electrical Characteristics

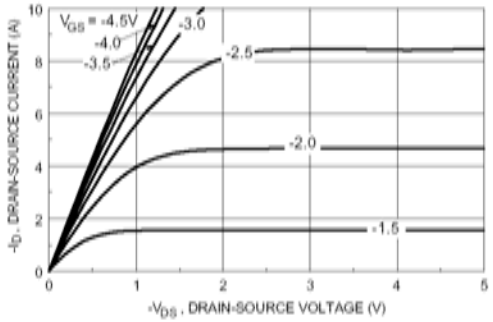


Figure 1. On-Region Characteristics.

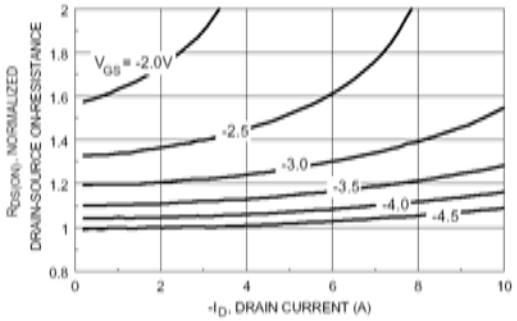


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

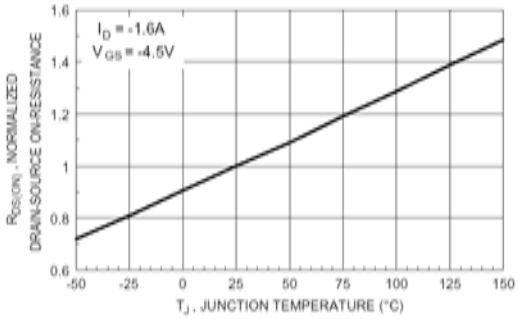


Figure 3. On-Resistance Variation with Temperature.

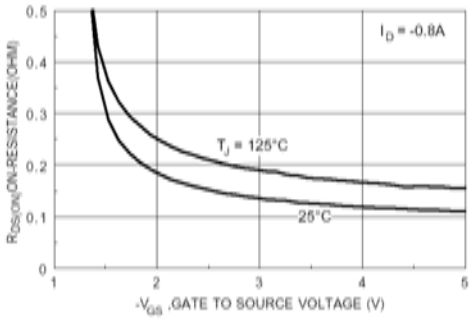


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

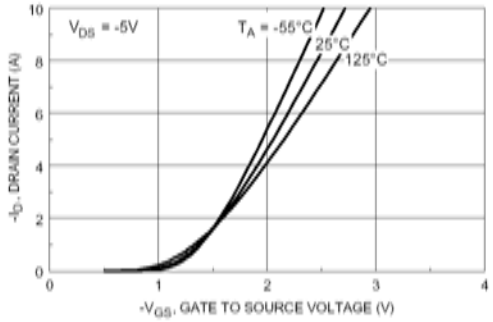


Figure 5. Transfer Characteristics.

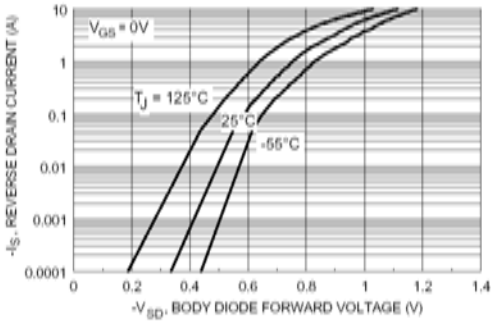


Figure 6 . Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical Characteristics

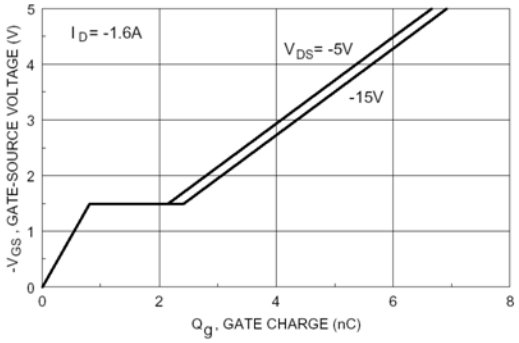


Figure 7. Gate Charge Characteristics.

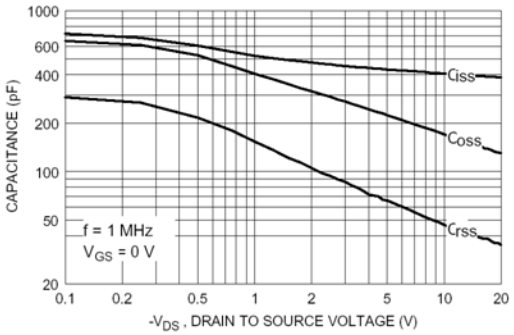


Figure 8. Capacitance Characteristics.

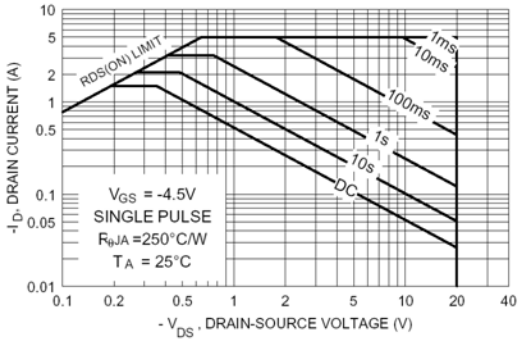


Figure 9. Maximum Safe Operating Area.

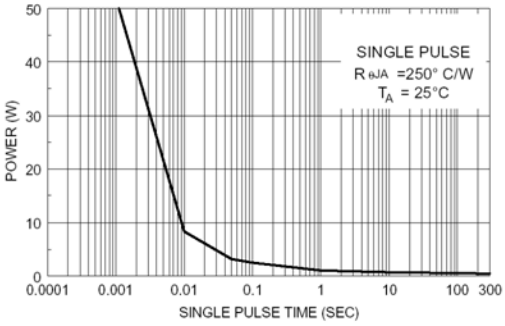


Figure 10. Single Pulse Maximum Power Dissipation.

Normalized Thermal Transient Junction to Ambient

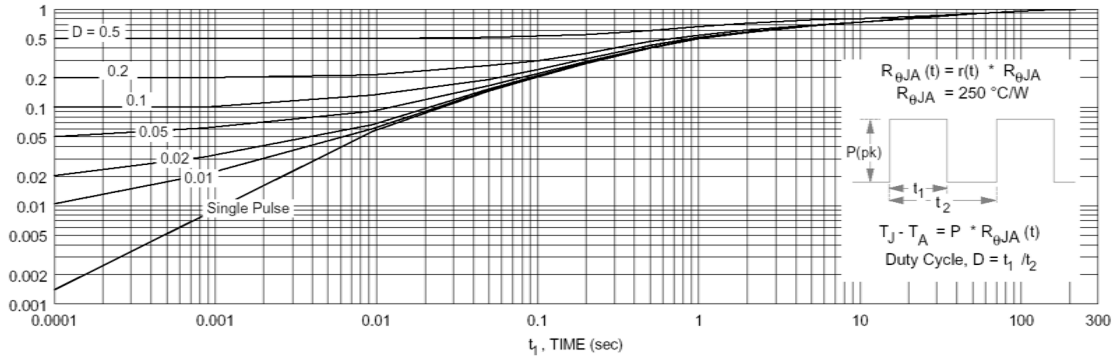
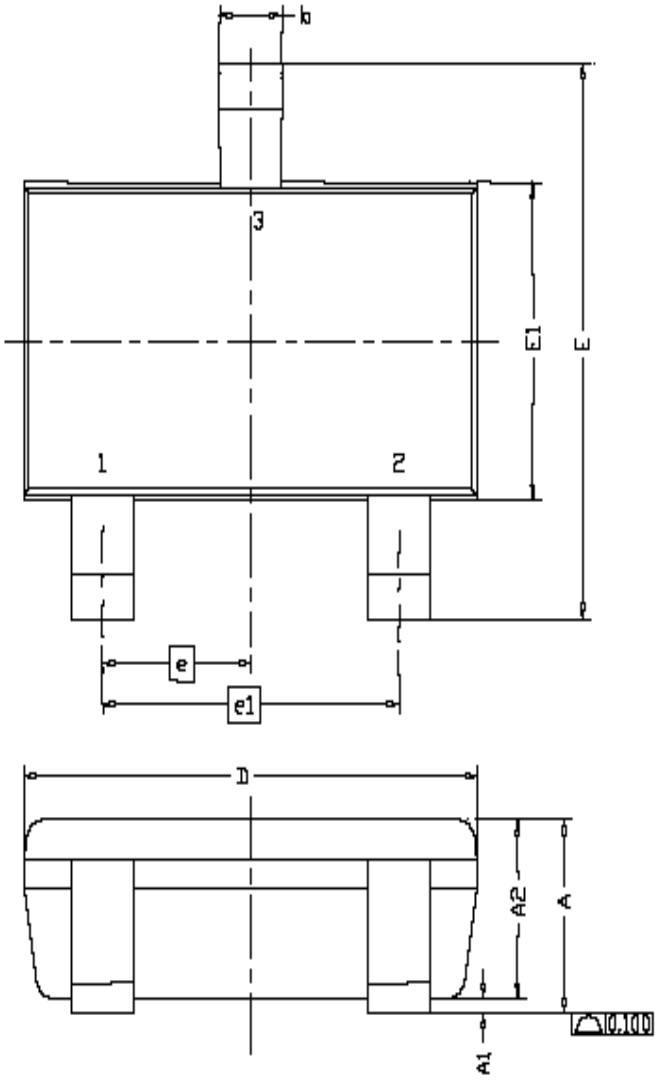


Figure 11. Transient Thermal Response Curve.

Package Information



DIM.	MILLIMETERS		
	MIN	NOM	MAX
A	0.935	0.95	1.10
A1	0.01	---	0.10
A2	0.85	0.90	0.925
b	0.30	0.40	0.50
c	0.10	0.15	0.25
D	2.70	2.90	3.10
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e	0.95 BSC		
e1	1.90 BSC		
L	0.30	0.40	0.60
L1	0.60REF		
L2	0.25BSC		
R	0.10	---	---
θ	0°	4°	8°
θ1	7°NOM